TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVI)

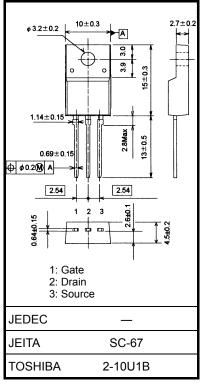
# 2SK3563

#### Switching Regulator Applications

- Low drain-source ON resistance: R<sub>DS</sub> (ON) = 1.35 Ω (typ.)
- High forward transfer admittance: |Y<sub>fs</sub>| = 3.5 S (typ.)
- Low leakage current: I<sub>DSS</sub> = 100 μA (max) (V<sub>DS</sub> = 500 V)
- Enhancement mode:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	500	V	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	500	V	
Gate-source voltage		V <sub>GSS</sub>	±30	V	
Drain current	DC (Note 1)	۱ <sub>D</sub>	5		
	Pulse (t = 1 ms) (Note 1)	I <sub>DP</sub>	20	A	
Drain power dissipati	on (Tc = 25°C)	PD	35	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	180	mJ	
Avalanche current		I <sub>AR</sub>	5	А	
Repetitive avalanche energy (Note 3)		E <sub>AR</sub>	3.5	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	



Weight : 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

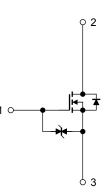
Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	3.57	°C/W	
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	62.5	°C/W	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 90 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}(\text{initial}), \text{ L} = 12.2 \text{ mH}, \text{ I}_{AR} = 5 \text{ A}, \text{ R}_{G} = 25 \Omega$ 

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



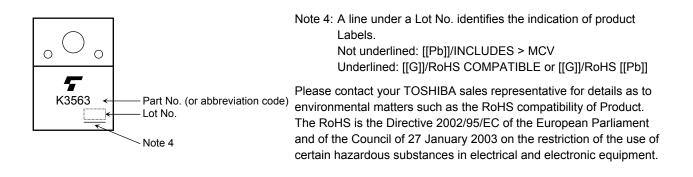
**Electrical Characteristics (Ta = 25°C)** 

Char	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS}=\pm 25~V,~V_{DS}=0~V$			±10	μA
Gate-source brea	akdown voltage	V (BR) GSS	$I_G=\pm 10~\mu A,~V_{DS}=0~V$	±30		_	V
Drain cut-off curr	ent	IDSS	$V_{DS} = 500 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			100	μA
Drain-source bre	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	500		_	V
Gate threshold ve	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2.0		4.0	V
Drain-source ON	resistance	R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 2.5 \text{ A}$		1.35	1.50	Ω
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 2.5 \text{ A}$	1.5	3.5		S
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		550		pF
Reverse transfer capacitance		C <sub>rss</sub>			7	_	
Output capacitance		C <sub>oss</sub>	1		70		
Switching time	Rise time	tr	$V_{GS} = 2.5 \text{ A V}_{OUT}$ $V_{GS} = 15 \Omega$ $V_{DD} \approx 225 \text{ V}$ $V_{DD} \approx 225 \text{ V}$ $P_{UT} = 10 \mu \text{ s}$	_	10	_	
	Turn-on time	t <sub>on</sub>			20	_	
	Fall time	t <sub>f</sub>		_	10	_	ns
	Turn-off time	t <sub>off</sub>		_	50	_	
Total gate charge		Qg			16	—	
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \simeq 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 5 \text{ A}$		10	_	nC
Gate-drain charge		Q <sub>gd</sub>	]		6		

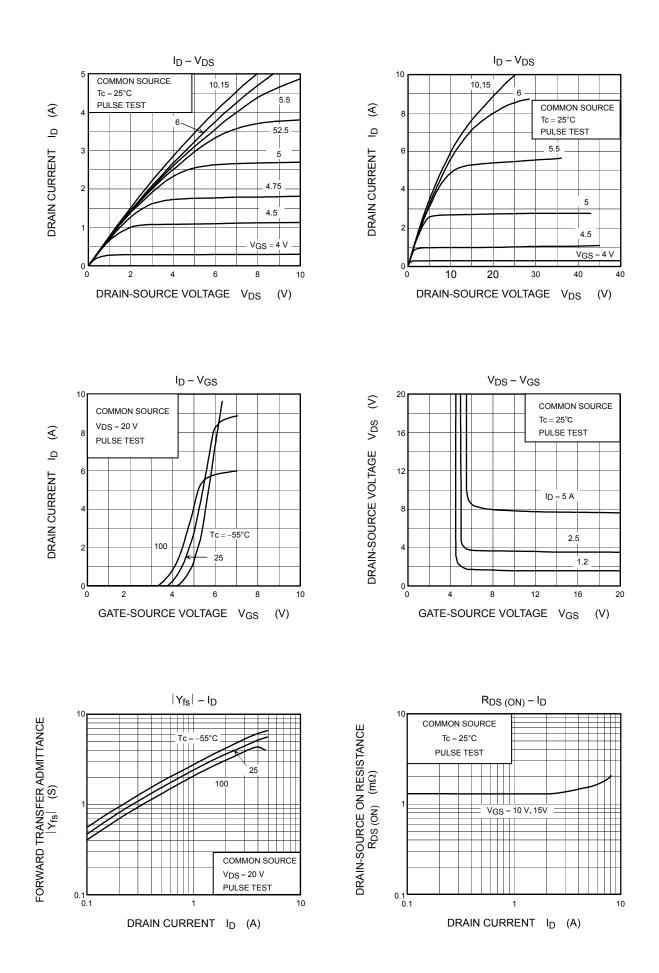
#### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	_	_	5	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	_	_	20	А
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	$I_{DR} = 5 \text{ A}, V_{GS} = 0 \text{ V},$	_	1400	_	ns
Reverse recovery charge	Q <sub>rr</sub>	dl <sub>DR</sub> /dt = 100 A/μs	_	9	_	μC

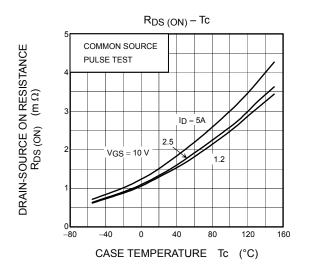
#### Marking

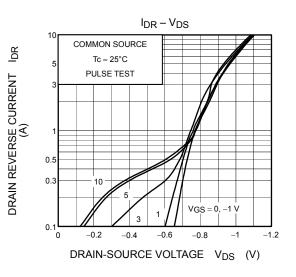


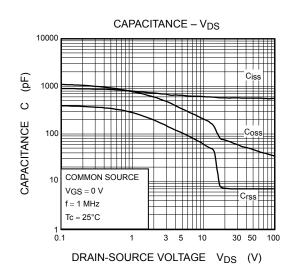
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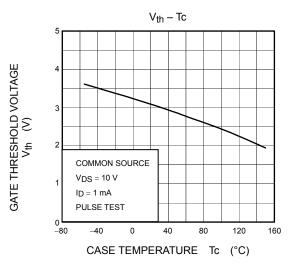


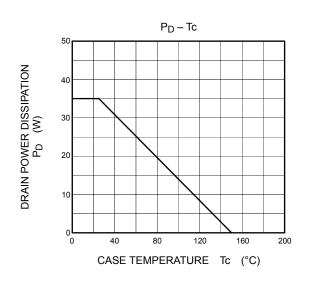
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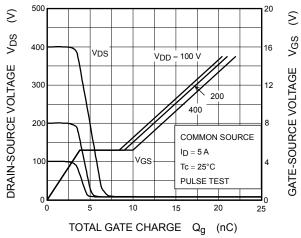


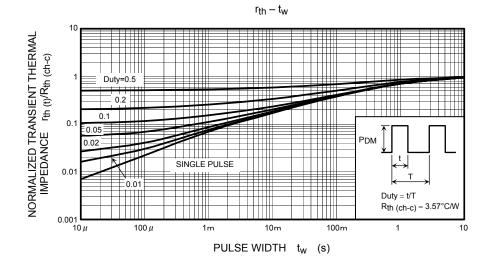


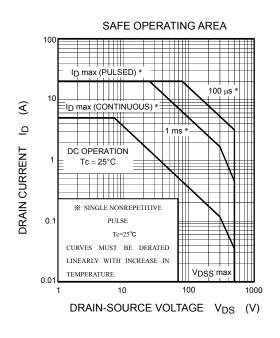


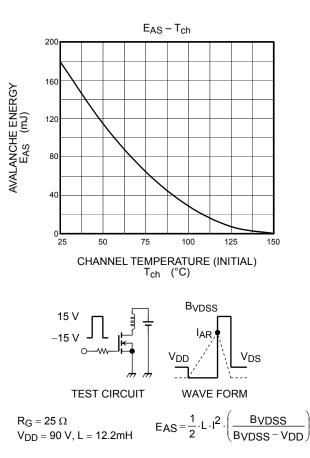












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